

MOS FIELD EFFECT TRANSISTOR 2SJ598

SWITCHING P-CHANNEL POWER MOS FET

DESCRIPTION

The 2SJ598 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

FEATURES

· Low on-state resistance:

 $R_{DS(on)1}$ = 130 m Ω MAX. (V_{GS} = -10 V, I_D = -6 A)

 $R_{DS(on)2} = 190 \text{ m}\Omega \text{ MAX}. (V_{GS} = -4.0 \text{ V}, I_D = -6 \text{ A})$

- Low Ciss: Ciss = 720 pF TYP.
- · Built-in gate protection diode
- TO-251/TO-252 package

★ ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SJ598	TO-251 (MP-3)		
2SJ598-Z	TO-252 (MP-3Z)		

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

VDSS	-60	V
Vgss	∓20	V
I _{D(DC)}	∓12	Α
I _{D(pulse)}	∓30	Α
Рт	23	W
Рт	1.0	W
Tch	150	°C
T _{stg}	-55 to +150	°C
las	–12	Α
Eas	14.4	mJ
	VGSS ID(DC) ID(pulse) PT PT Tch Tstg IAS	VGSS ∓20 ID(DC) ∓12 ID(pulse) ∓30 PT 23 PT 1.0 Tch 150 Tstg −55 to +150 IAS −12

(TO-251)



TO-252)



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = -30 V, R_G = 25 Ω , V_{GS} = -20 \rightarrow 0 V

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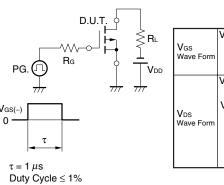
ELECTRICAL CHARACTERISTICS (TA = 25°C)

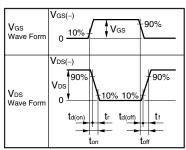
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -60 V, V _{GS} = 0 V			-10	μΑ
Gate Leakage Current	Igss	V _{GS} = ∓16 V, V _{DS} = 0 V			∓10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-1.5	-2.0	-2.5	٧
Forward Transfer Admittance	y fs	V _{DS} = -10 V, I _D = -6 A	5	11		S
Drain to Source On-state Resistance	RDS(on)1	V _{GS} = -10 V, I _D = -6 A		102	130	mΩ
	RDS(on)2	V _{GS} = -4.0 V, I _D = -6 A		131	190	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V		720		pF
Output Capacitance	Coss	V _{GS} = 0 V		150		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		50		pF
Turn-on Delay Time	t d(on)	I _D = -6 A		7		ns
Rise Time	tr	V _{GS} = -10 V		4		ns
Turn-off Delay Time	t _{d(off)}	V _{DD} = -30 V		35		ns
Fall Time	tf	$R_G = 0 \Omega$		10		ns
Total Gate Charge	Q _G	I _D = -12 A		15		nC
Gate to Source Charge	Qgs	V _{DD} = -48 V		3		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = -10 V		4		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 12 A, V _{GS} = 0 V		0.98		٧
Reverse Recovery Time	trr	I _F = 12 A, V _{GS} = 0 V		50		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A /μs		100		nC

TEST CIRCUIT 1 AVALANCHE CAPABILITY

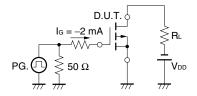
$V_{GS} = -20 \rightarrow 0 \text{ V}$ V_{DD} V_{DD}

TEST CIRCUIT 2 SWITCHING TIME



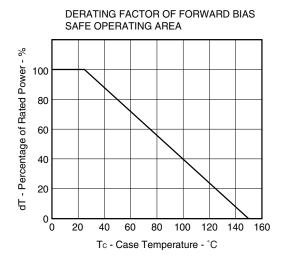


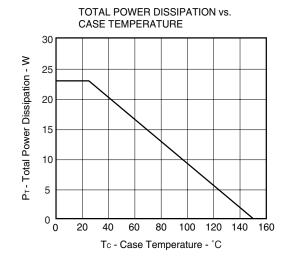
TEST CIRCUIT 3 GATE CHARGE



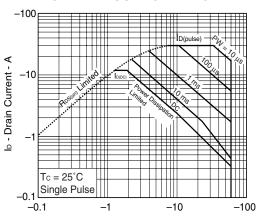


TYPICAL CHARACTERISTICS (TA = 25°C)



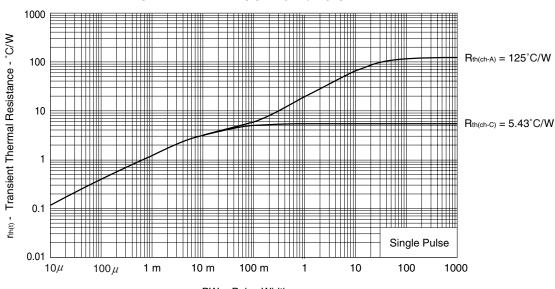


FORWARD BIAS SAFE OPERATING AREA



V_{DS} - Drain to Source Voltage - V

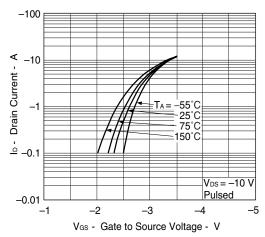
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



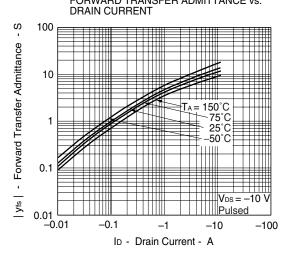
PW - Pulse Width - s

3

FORWARD TRANSFER CHARACTERISTICS

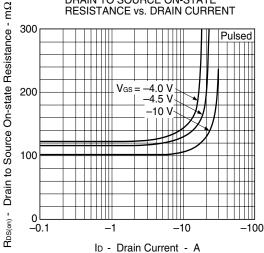


FORWARD TRANSFER ADMITTANCE vs.

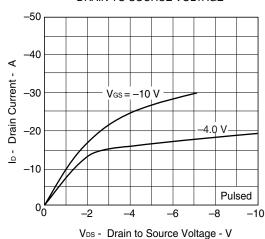


RESISTANCE vs. DRAIN CURRENT 300

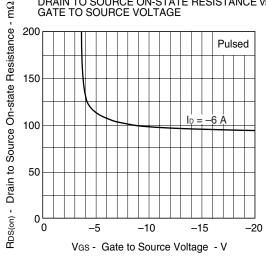
DRAIN TO SOURCE ON-STATE



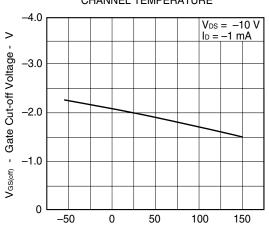
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

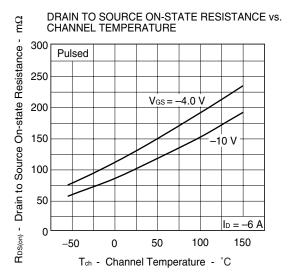


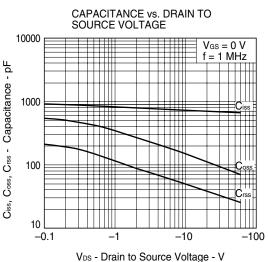
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

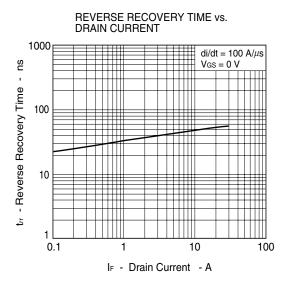


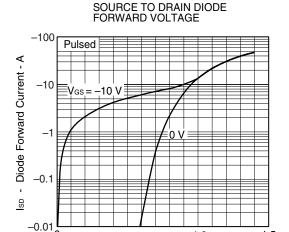
Tch - Channel Temperature - °C











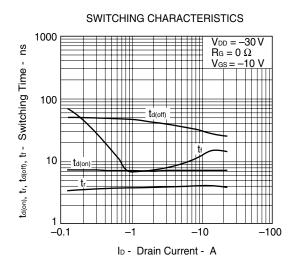
-0.5

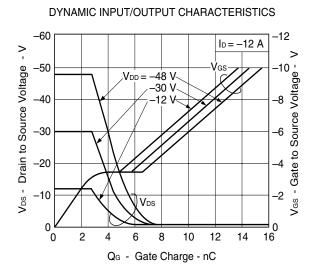
Vsp - Source to Drain Voltage - V

-1.0

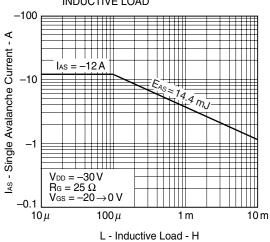
-1.5

0

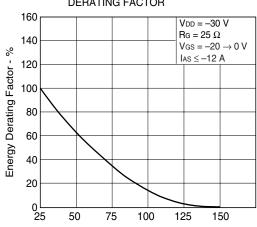




SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



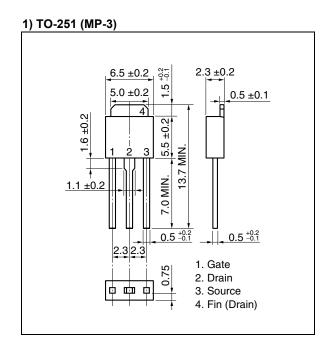
SINGLE AVALANCHE ENERGY DERATING FACTOR

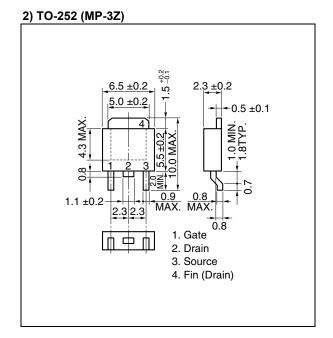


Starting Tch - Starting Channel Temperature - °C

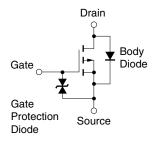


★ PACKAGE DRAWINGS (Unit: mm)





EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Data Sheet D14656EJ4V0DS 7

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